

2N7002BK

60 V, 350 mA N-channel Trench MOSFET Rev. 1 — 17 June 2010

Product data sheet

Product profile

1.1 General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

1.2 Features and benefits

- Logic-level compatible
- Very fast switching
- Trench MOSFET technology
- ESD protection up to 2 kV
- AEC-Q101 qualified

1.3 Applications

- Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DS}	drain-source voltage	$T_{amb} = 25 ^{\circ}C$	-	-	60	V
V_{GS}	gate-source voltage	T _{amb} = 25 °C	-	-	±20	V
I _D	drain current	T_{amb} = 25 °C; V_{GS} = 10 V	[1] -	-	350	mA
R _{DSon}	drain-source on-state resistance	$T_j = 25 ^{\circ}\text{C};$ $V_{GS} = 10 \text{V};$ $I_D = 500 \text{mA}$	-	1	1.6	Ω

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².



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2. Pinning information

Table 2. Pinning

Table 2.	i iiiiiiig			
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		5
2	S	source	<u> </u>	D
3	D	drain	1 2	G

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
2N7002BK	TO-236AB	plastic surface-mounted package; 3 leads	SOT23

4. Marking

Table 4. Marking codes

Type number	Marking code ^[1]
2N7002BK	LN*

[1] * = -: made in Hong Kong

* = p: made in Hong Kong

* = t: made in Malaysia

* = W: made in China

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	$T_{amb} = 25 ^{\circ}C$	-	60	V
V_{GS}	gate-source voltage	T _{amb} = 25 °C	-	±20	V
I_D	drain current	$V_{GS} = 10 \text{ V}$	<u>[1]</u>		
		T _{amb} = 25 °C	-	350	mA
		T _{amb} = 100 °C	-	245	mA
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$	-	1.2	Α

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 Table 5.
 Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2] -	370	mW
			[1] -	440	mW
		T _{sp} = 25 °C	-	1.2	W
Tj	junction temperature			150	°C
T _{amb}	ambient temperature		-55	+150	°C
T _{stg}	storage temperature		-65	+150	°C
Source-d	rain diode				
Is	source current	T _{amb} = 25 °C	[1] -	350	mA
ESD max	imum rating				
V _{ESD}	electrostatic discharge voltage	human body model	[3] -	2000	V

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- [3] Measured between all pins.

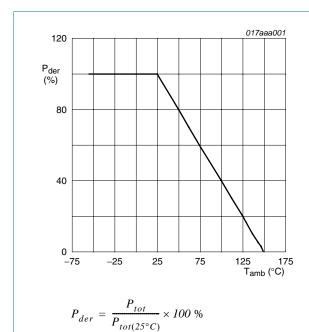
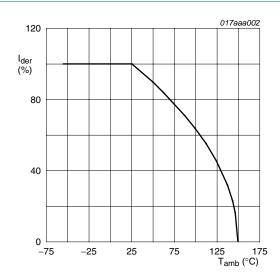


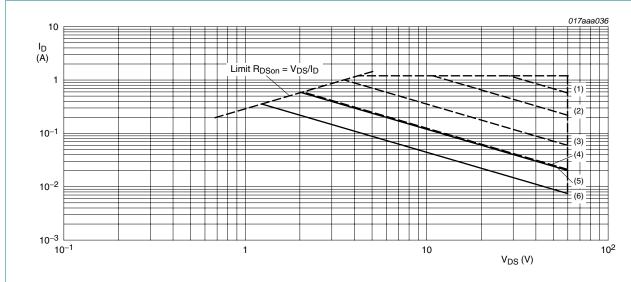
Fig 1. Normalized total power dissipation as a function of ambient temperature



$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

Fig 2. Normalized continuous drain current as a function of ambient temperature

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I_{DM} = single pulse

- (1) $t_p = 100 \mu s$
- (2) $t_p = 1 \text{ ms}$
- (3) $t_p = 10 \text{ ms}$
- (4) $t_D = 100 \text{ ms}$
- (5) DC; $T_{sp} = 25 \, ^{\circ}\text{C}$
- (6) DC; $T_{amb} = 25 \, ^{\circ}C$; drain mounting pad 1 cm²

Fig 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

6. Thermal characteristics

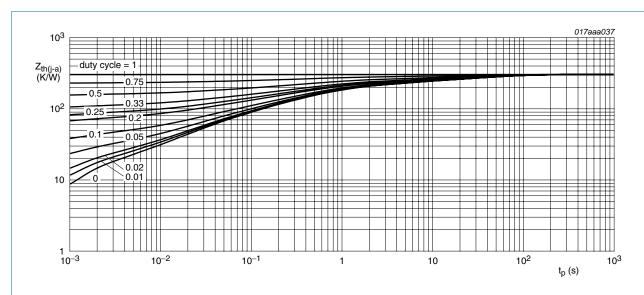
Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from	in free air	<u>[1]</u> -	295	340	K/W
	junction to ambient		[2] _	250	285	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point		-	-	105	K/W

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

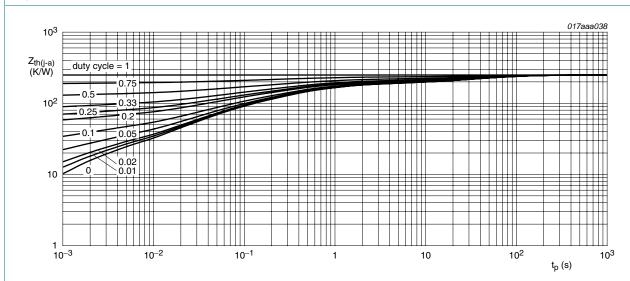
^[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².

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FR4 PCB, standard footprint

Fig 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for drain 1 cm²

Fig 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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7. Characteristics

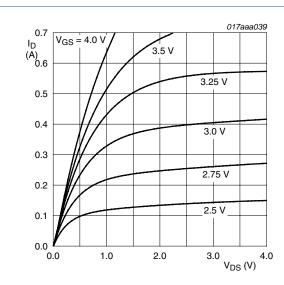
Table 7. Characteristics

 $T_i = 25$ °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 10 \mu A; V_{GS} = 0 V$	60	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 250 \ \mu A; \ V_{DS} = V_{GS}$	1.1	1.6	2.1	V
I _{DSS}	drain leakage current	$V_{DS} = 60 \text{ V}; V_{GS} = 0 \text{ V}$				
		T _j = 25 °C	-	-	1	μΑ
		T _j = 150 °C	-	-	10	μΑ
I _{GSS}	gate leakage current	$V_{GS} = \pm 20 \text{ V}; V_{DS} = 0 \text{ V}$	-	-	10	μΑ
R_{DSon}	drain-source on-state		<u>[1]</u>			μΑ Ω Ω mS
	resistance	V_{GS} = 5 V; I_D = 50 mA	- 1 1.6 Ω	Ω		
		$V_{GS} = 10 \text{ V}; I_D = 500 \text{ mA}$	-	1	1.6	Ω
g _{fs}	forward transconductance	$V_{DS} = 10 \text{ V}; I_D = 200 \text{ mA}$	[1] _	550	-	mS
Dynamic o	characteristics					
Q _{G(tot)}	total gate charge	$I_D = 300 \text{ mA};$	-	0.5	0.6	nC
Q_{GS}	gate-source charge		-	0.2	-	nC
Q_{GD}	gate-drain charge	VGS = 4.5 V	-	0.1	-	nC
C _{iss}	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 10 \text{ V};$	-	33	50	рF
C _{oss}	output capacitance	$V_{GS} = \pm 20 \text{ V}; V_{DS} = 0 \text{ V} \qquad - \\ $	-	7	-	рF
C _{rss}	reverse transfer capacitance		-	4	-	pF
t _{d(on)}	turn-on delay time	$V_{DD} = 50 \text{ V};$	-	5	10	ns
t _r	rise time	$R_L = 250 \Omega;$ - $V_{GS} = 10 V;$	-	6	-	ns
t _{d(off)}	turn-off delay time	$R_{G} = 6 \Omega$	-	12	24	ns
t _f	fall time	-	-	7	-	ns
Source-dr	ain diode					
V_{SD}	source-drain voltage	$I_S = 115 \text{ mA}; V_{GS} = 0 \text{ V}$	0.47	0.75	1.1	V

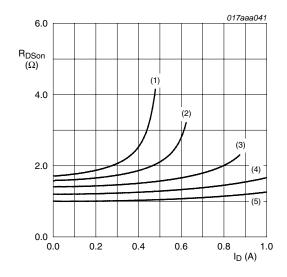
^[1] Pulse test: $t_p \le 300~\mu s;~\delta \le 0.01.$

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 $T_{amb} = 25 \, ^{\circ}C$

Fig 6. Output characteristics: drain current as a function of drain-source voltage; typical values



T_{amb} = 25 °C

(1) $V_{GS} = 3.25 \text{ V}$

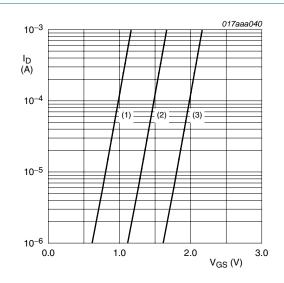
(2) $V_{GS} = 3.5 \text{ V}$

(3) $V_{GS} = 4 V$

(4) $V_{GS} = 5 \text{ V}$

(5) $V_{GS} = 10 \text{ V}$

Fig 8. Drain-source on-state resistance as a function of drain current; typical values



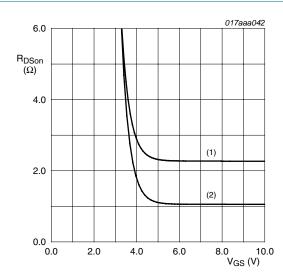
 T_{amb} = 25 °C; V_{DS} = 5 V

(1) minimum values

(2) typical values

(3) maximum values

Fig 7. Sub-threshold drain current as a function of gate-source voltage



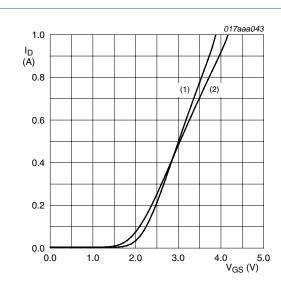
 $I_D = 500 \text{ mA}$

(1) $T_{amb} = 150 \, ^{\circ}C$

(2) $T_{amb} = 25 \, ^{\circ}C$

Fig 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

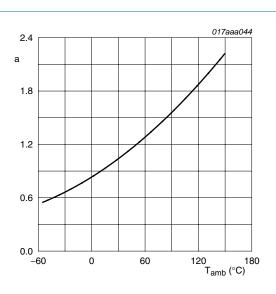
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$$V_{DS} > I_{D} \times R_{DSon}$$

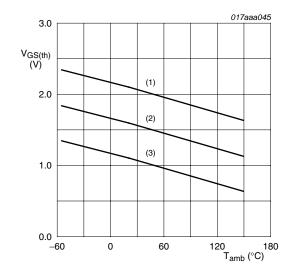
- (1) $T_{amb} = 25 \, ^{\circ}C$
- (2) $T_{amb} = 150 \, ^{\circ}C$

Fig 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values



$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

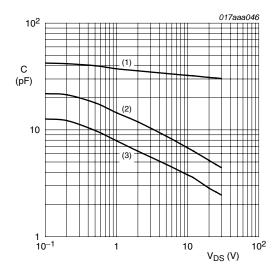
Fig 11. Normalized drain-source on-state resistance as a function of ambient temperature; typical values



 $I_D = 0.25 \text{ mA}; V_{DS} = V_{GS}$

- (1) maximum values
- (2) typical values
- (3) minimum values

Fig 12. Gate-source threshold voltage as a function of ambient temperature

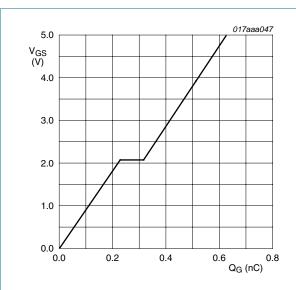


f = 1 MHz; V_{GS} = 0 V

- (1) C_{iss}
- (2) Coss
- $(3) \quad C_{rss}$

Fig 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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 I_D = 300 mA; V_{DD} = 6 V; T_{amb} = 25 °C

Fig 14. Gate-source voltage as a function of gate charge; typical values

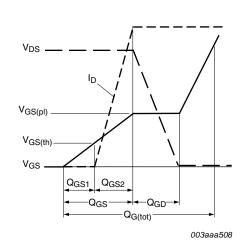
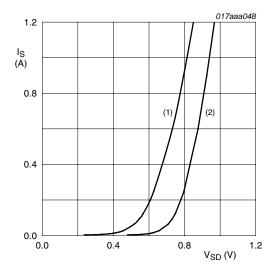


Fig 15. Gate charge waveform definitions



 $V_{GS} = 0 V$

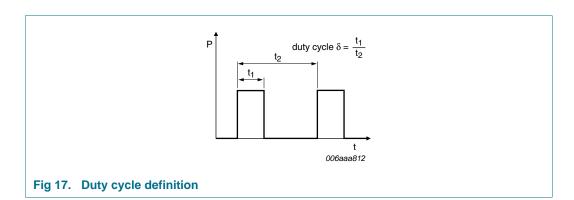
(1) $T_{amb} = 150 \, ^{\circ}C$

(2) $T_{amb} = 25 \, ^{\circ}C$

Fig 16. Source current as a function of source-drain voltage; typical values

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8. Test information



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9. Package outline

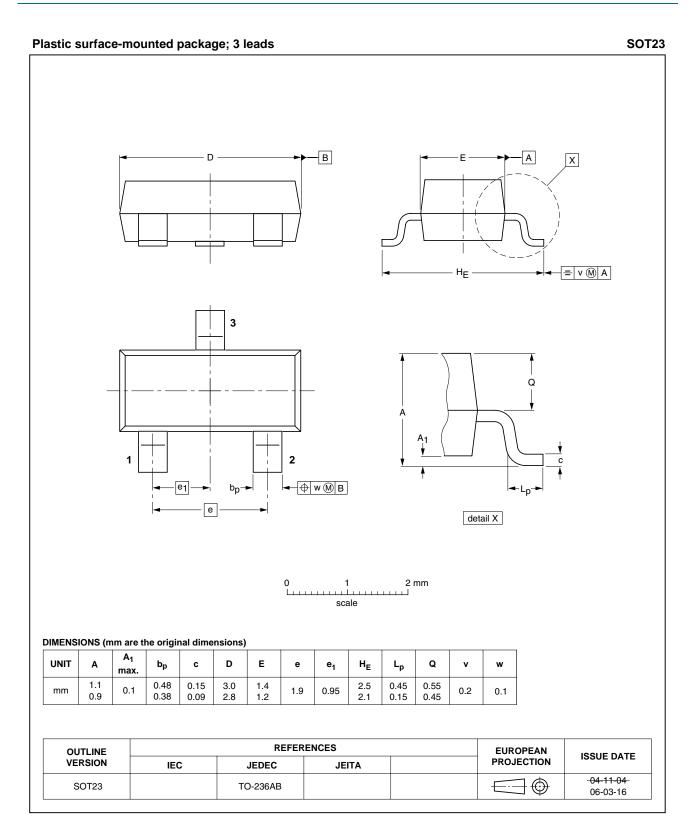
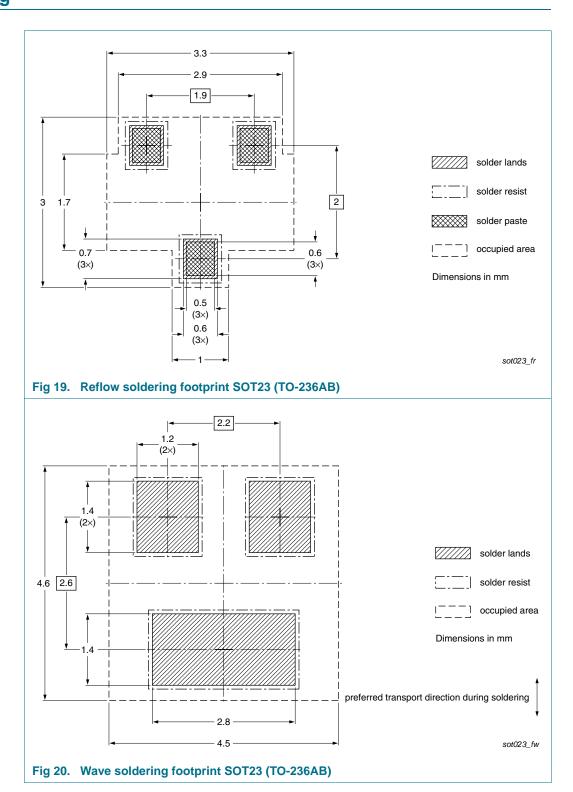


Fig 18. Package outline SOT23 (TO-236AB)

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10. Soldering



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11. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
2N7002BK v.1	20100617	Product data sheet	-	-

60 V, 350 mA N-channel Trench MOSFET

12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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Quick reference data — The Quick reference data is an extract of the product data given in the Limiting values and Characteristics sections of this document, and as such is not complete, exhaustive or legally binding.

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